What is claimed is:

1.   An image sensor, comprising:

a plurality of units, each unit associated with

5   accepting a pixel of an image, and each unit having a

photoreceptor therein, a follower transistor, connected to

said photoreceptor, a select transistor connected to said

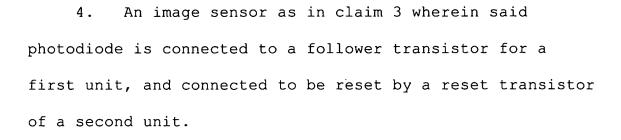photoreceptor, and a reset transistor which controls

applying a reset level;

10   a first bias line providing power to at least one of

said transistors for a first unit, and a second bias line

providing power to another of said transistors, different

than said one of said transistors of said first unit, such

that said one and said another transistors are separately

15   powered by separate bias lines.

2.   An image sensor as in claim 1 wherein said first

bias line powers the follower transistor and said second

bias line powers a reset transistor.

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3.   An image sensor as in claim 1 wherein said

photoreceptor is a photodiode.

4.   An image sensor as in claim 3 wherein said photodiode is connected to a follower transistor for a first unit, and connected to be reset by a reset transistor of a second unit.

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5.   An image sensor as in claim 1 wherein said sensor is an active pixel sensor, formed of transistors which are compatible with CMOS techniques, and each of a plurality of pixels of which includes an in pixel follower transistor an

10   in pixel selection transistor and an in pixel reset transistor.

6.   An image sensor as in claim 5 wherein said select and reset transistors are connected to said first bias

15   source and said follower transistors connected to said second bias source.

7.   An image sensor as in claim 6 wherein said second bias source is connected commonly to a first plurality of

20   followers in a first row of said pixels and a second plurality of reset transistors in a second row of pixels different than said first row of pixels.

8.   An image sensor as in claim 1 wherein said photoreceptor is a photogate, and further comprising a floating diffusion portion in the substrate connected to said follower transistor, and further comprising a transfer gate, coupled between said photogate and said floating diffusion, which is activated to allow charge in said photogate to dump into said floating diffusion.

9.   An image sensor as in claim 8 further comprising a reset diffusion storing a reset level, and wherein said reset transistor is connected between said floating diffusion and said reset level.

10. An active pixel sensor comprising:

an array of photosensors, each element of the array including a photoreceptor, an in pixel follower connected to an output of said photoreceptor, and a select line connected to said follower transistor;

a reset transistor connected to reset a level of charge produced by said photoreceptor; and

a pair of biasing connections including a first biasing connection connected to said reset transistor, and a second biasing connection, separated from said first biasing connection, connected to said follower.

11. A sensor as in claim 10 wherein said photoreceptor is connected between a reset transistor of first line, and a follower of a second line different than

5   said first line.

12. A sensor as in claim 10 further comprising a dynamic mode read out transistor, associated with at least one of said biasing connections, and allowing said biasing

10   connection to be active for only a part, but not all, of a period.

13. A sensor as in claim 10 further comprising a connection which is activated to cause said pixels to be

15   referenced to a ground reference, and is opened to cause said pixels to be floated.

14. An active pixel sensor comprising:

an array of pixels, each pixel including a

20   photosensor, and at least first and second transistors associated with said photosensor in said each pixel, said first transistor connected to receive power from a first power supply source over a first line, and said second transistor connected to receive power from a second power

supply source over a second line totally separate from said

first power supply line.

15. A sensor as in claim 14, wherein said first

5   transistor and said second transistor have drains which are

not electrically connected.

16. A sensor as in claim 14, further comprising a

steady state current generator, providing a first, "on"

10 mode connecting the columns to ground and a second "off"

mode which provides floating columns.

17. A method of acquiring an image, comprising:

acquiring image pixels during a first part of a cycle;

15   resetting the level of charge that image pixels during

the second part of the cycle, wherein said reset level is

boosted during said second part of said cycle and not

during said first part of said cycle.

20   18. A method as in claim 17, wherein said resetting

comprises using a first bias source to bias a follower

transistor, and using a separate second bias source to bias

a reset transistor.

19. An image sensor, comprising:

a plurality of units, each unit associated with

accepting a pixel of an image, and each unit having a

photoreceptor therein, a follower transistor, connected to

5   said photoreceptor, a select transistor connected to said

photoreceptor, and a reset transistor which controls

applying a reset level a unit that is different than the

unit in which said reset transistor is physically located.

10   20. An image sensor as in claim 19, further

comprising

a first line controlling a selection of said unit; and

a second line providing bias for said unit.

15   21. An image sensor as in claim 19, wherein said

second line provides bias for a follower of a first unit

and for a reset level associated with a second unit.

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